

Photolithography and Chemical etching

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Definition of Photolithography

A process involving the photographic transfer of a pattern to a surface for etching

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History of photolithography

Lithography

Invented by Aloys Senefelder, 1796 (Germany) lithography (greek lithos: stone and graphein: write) technique based on a special use of limestone to multireplicate an image on paper

Photography

Albert Magnus (Germany) (1193–1280) discovered silver nitrate (light sensitive compound)

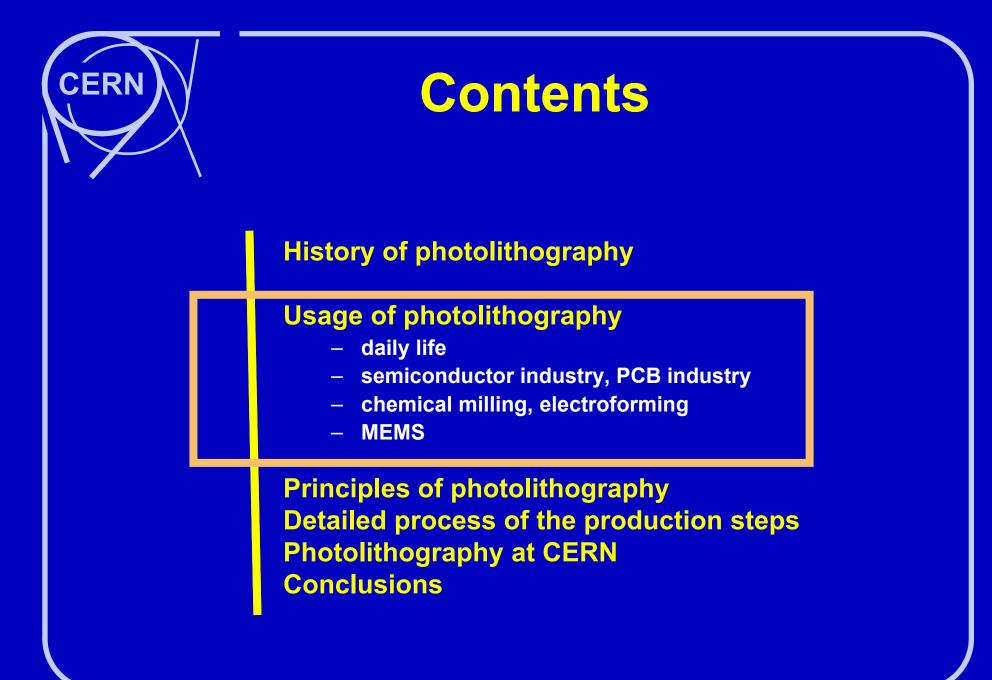
The first permanent photograph was an image produced in 1826 by the French inventor Nicéphore Niépce

Photolithography

Alphonse Louis Poitevin (France) invented photolithography in 1855

1935- Louis Minsk of Eastman Kodak developed the first negative photoresist

1940- Otto Suess of Kalle Div. of Hoechst AG, developed the first positive photoresist



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Daily life

All electronics boards and components



Offset lithography or offset printing

Lots of pictures are made by the help of photolithography: posters, screen printed images

Special products like:

- LCD displays
- Heads for inkjet printers
- Accelerator sensors for air bag ignition

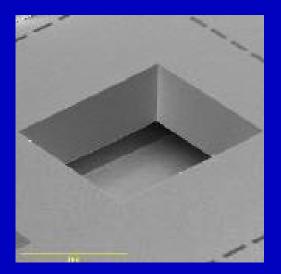




Semiconductor industry

Creation of metal lines for interconnection Mask areas for selective dopings Patterning of protective layers Micromachining of silicon

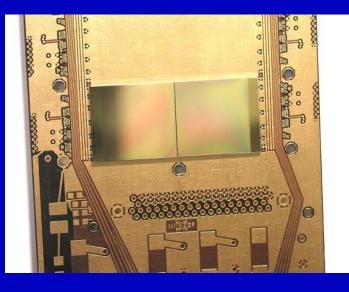


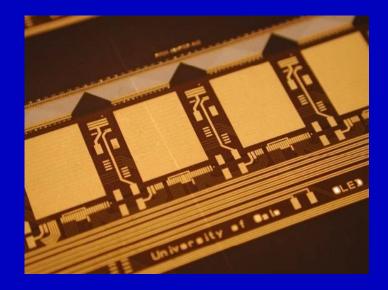




PCB industry

Creating all the conductive tracks Protective layers (soldermask) Legend ink layer Micro via generation





Chemical milling and electroforming

Wave guides
Heat sinks
Decorative items
Ink jet nozzles
Optical parts
Fuel cell parts
Micro sprockets
Lead frames
Encoder discs
Name plates
Flow sensors

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Thin metal plates +







MEMS micro electro mechanical systems



Main applications

- Ink jet printer heads
 - Pressure sensors
 - Accelerometers (automotive, gaming)
 - **Micro motors**
 - Magnetic sensors and actuators by electroforming magnetic materials



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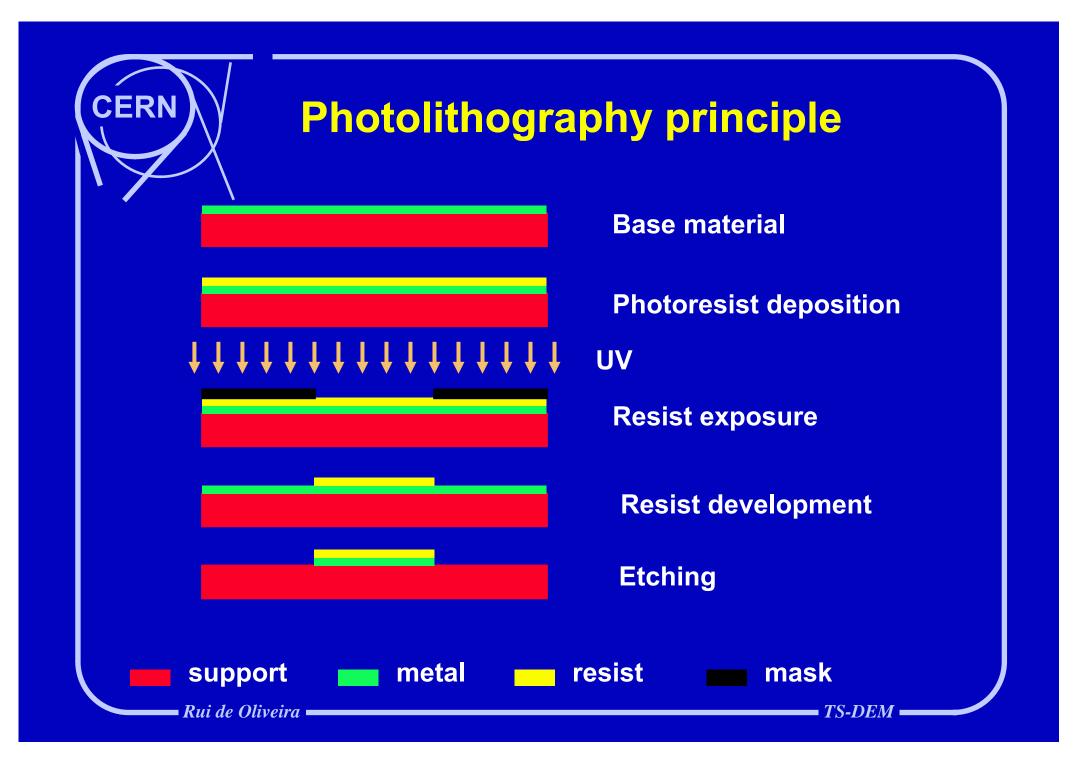
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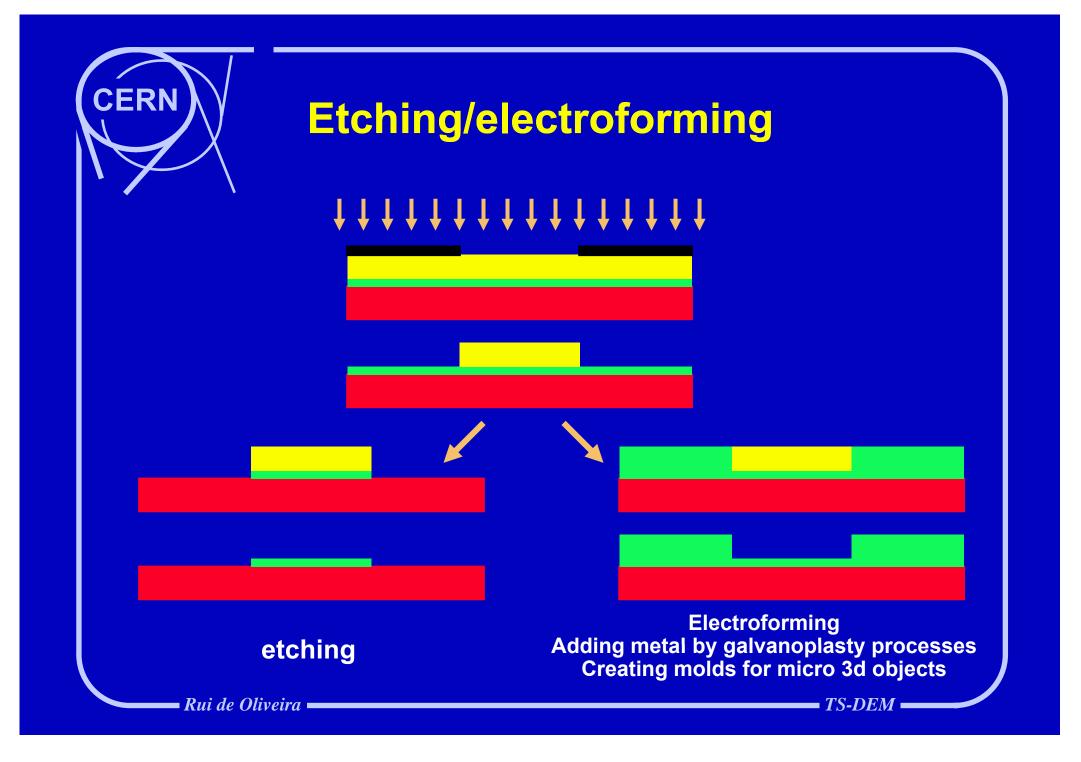
Principles of photolithography

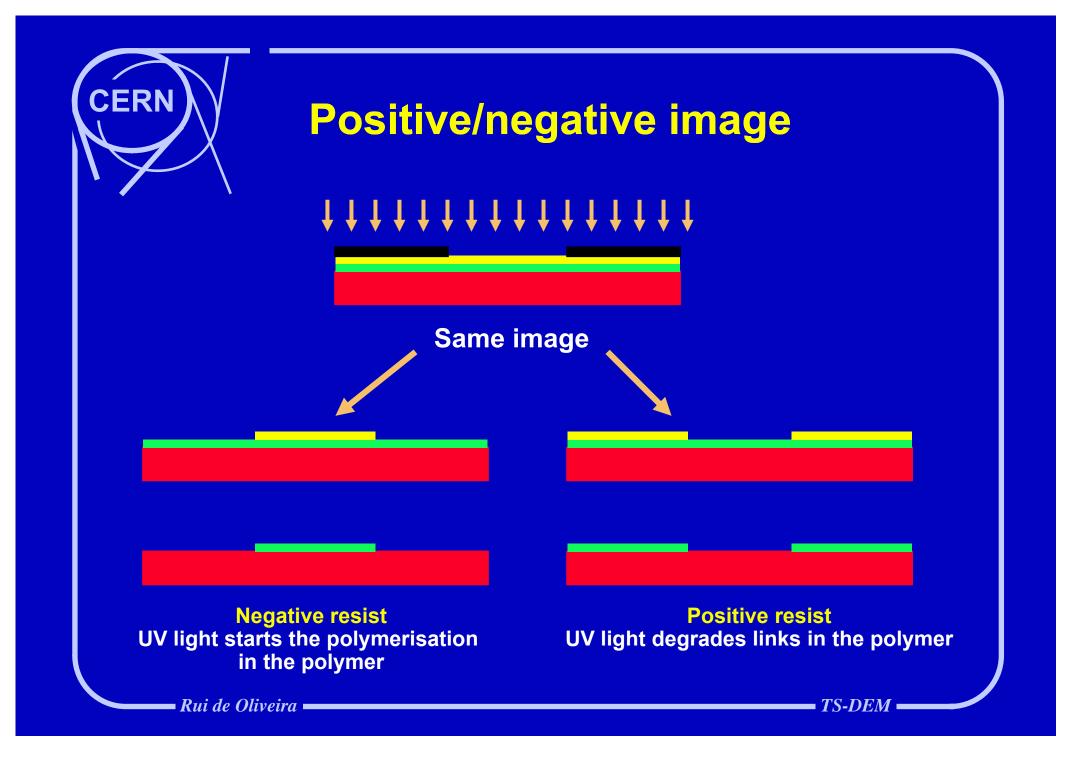
- principle
- etching/ electroforming
- positive/ negative images and resists

Detailed process of the production steps Photolithography at CERN Conclusions











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Detailed process of the production steps

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- Artwork
- Resist deposition
- Exposure 3 problems
- Resist development
- Etching

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Artwork generation

Glass masks (sub micron precision) 20 cm x 20 cm

- photographic emulsion on soda lime glass (cheapest)
- Fe₂O₃ on soda lime glass
- Cr on soda lime glass
- Cr on quartz glass (most expensive, needed for deep UV litho)

Polyester films (10 um precision) 80 cm x 60 cm – Laser exposure of a photosensitive layer on a polyester film





Resist deposition

Spinning - semiconductor production

Highest resolution

FRN

- Dip coating fine lines for PCBs or 3D objects
 - Fine lines, large sizes
- Curtain coating solder mask deposition
 - Fast, not accurate, cheap
- **Spray** liquid resist, solder mask deposition

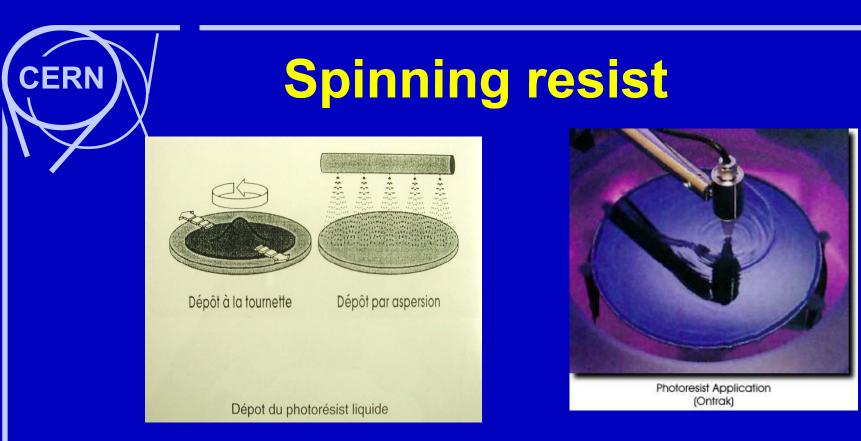
- 3d best coverage, best quality for solder mask

- Screen printing solder mask deposition
 - Medium quality solder mask, fast when the image is directly printed without photolithography

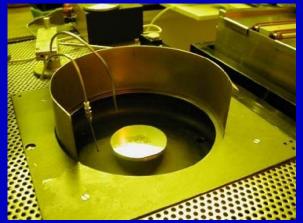
Dry film lamination- PCB production

- Fast, good resolution

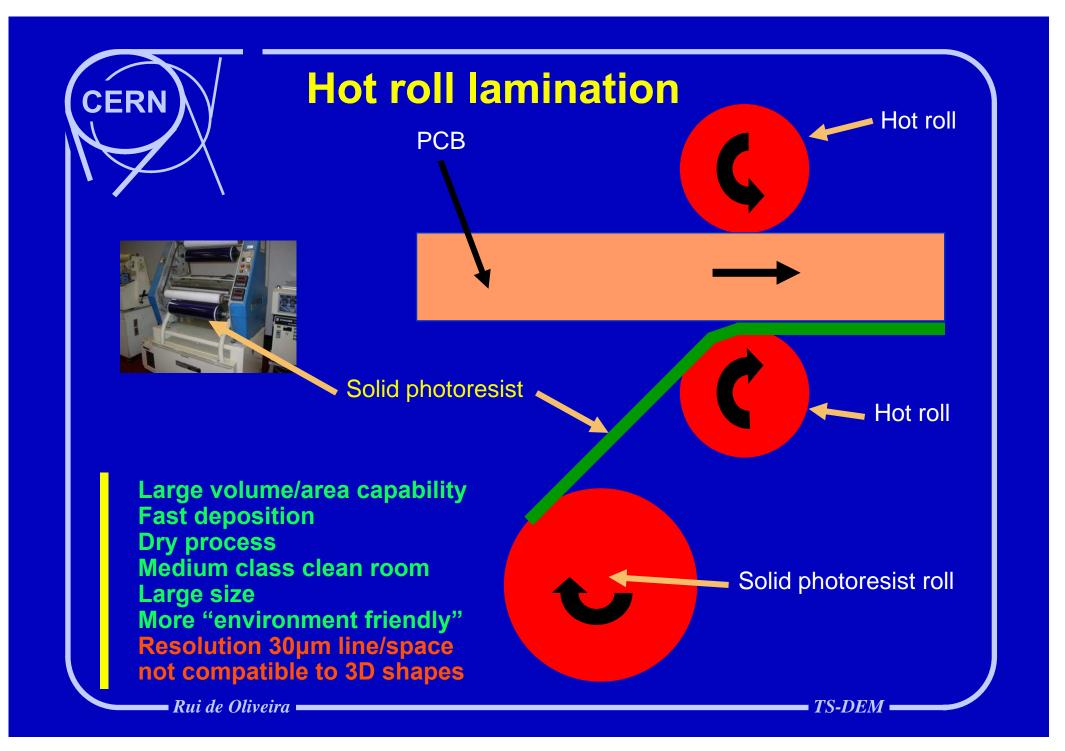
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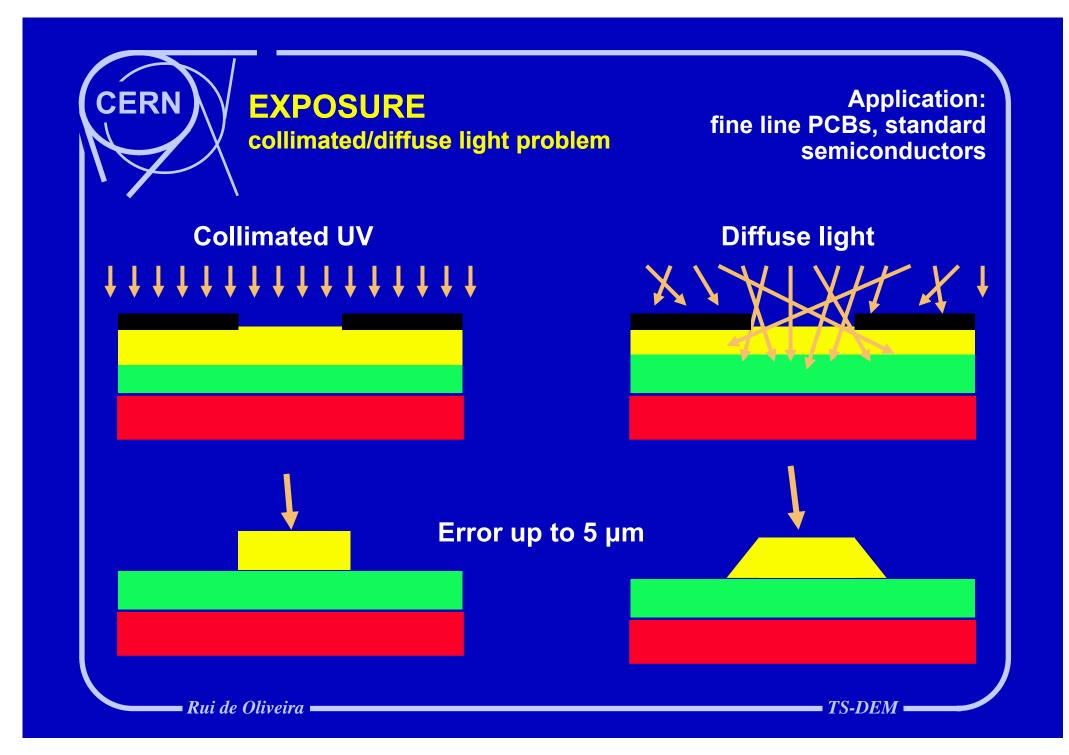


Very precise deposition Uniform thickness Ultra thin :down to 1 µm Large window in the process Good repeatability Clean rooms needed class 100 to 1 Solvent based resists



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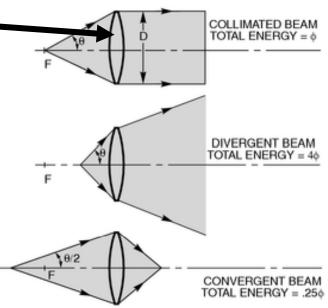
Collimated UV lamps



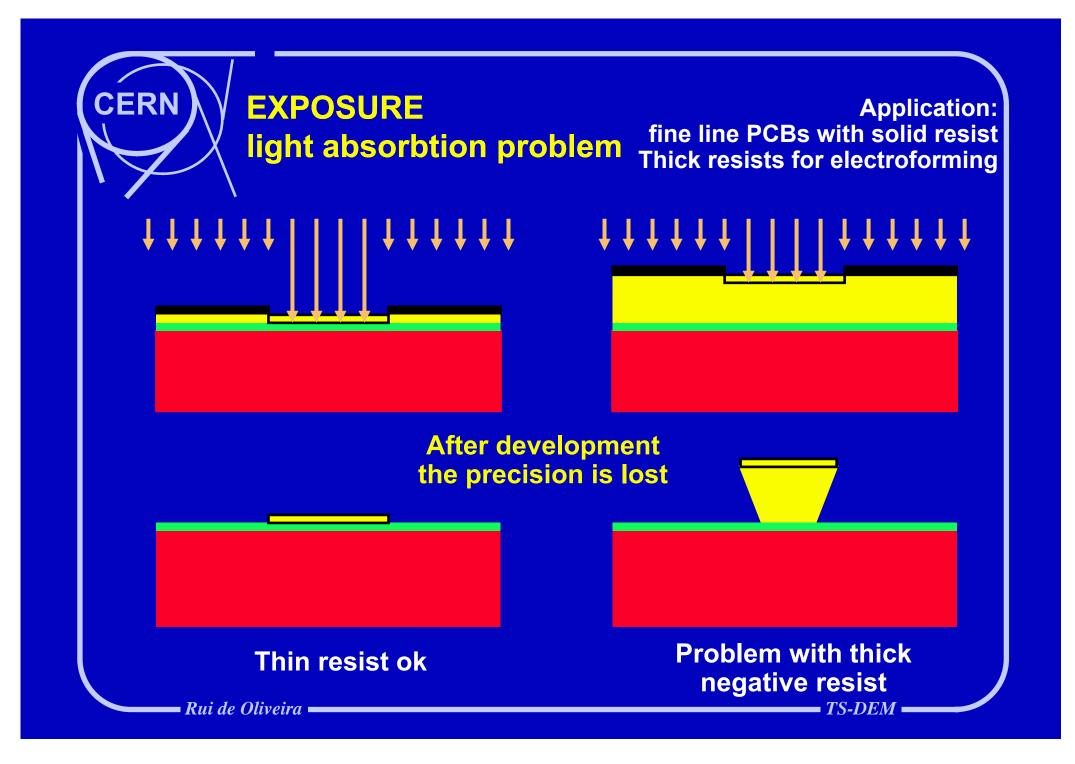
Precise large size lens up to 12 inches

The lens quality is the base of this system





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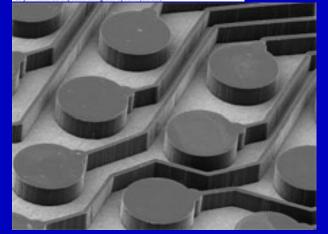


Laser UV direct exposure



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Figure 2 e 3 – The Paragon-8000 Laser Direct Imaging system (above) and 25 µm features exposed using this system (below)



25 μm lines 100 μm thick resist UV direct exposure No mask! resist

Increasing local energy can beat light absorbtion in the resist Precision: 0.5 μm to 2 μm (depending on laser type)

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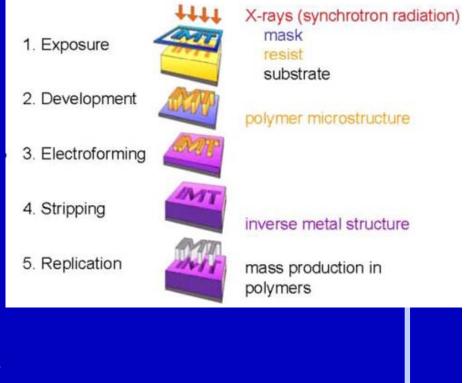
X ray exposure 'LIGA'

<u>LIGA</u> technology uses X<u>-ray lithography</u> to obtain polymer structures with extremely high aspect ratios (lateral precision bellow <u>1µm in a 0.1 to 2mm thick polymer</u>).

LIGA, a German acronym for "Lithographie, Galvanoformung, Abformung,"in English (X-ray) Lithography, Electroplating, and Molding.

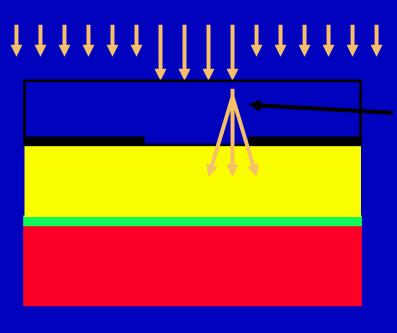
Because of the high collimation of X-rays needed, the source must be <u>synchrotron</u> <u>light</u>

This technology is the base of many MEMS, It beats the <u>limitation of light absorbtion</u> in the photoresist



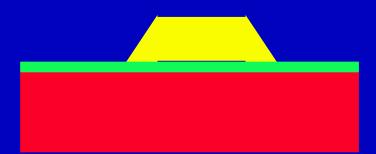


EXPOSURE light diffraction problem Ultra thin patterns Semiconductor prototypes



Diffraction in glass Less with quartz

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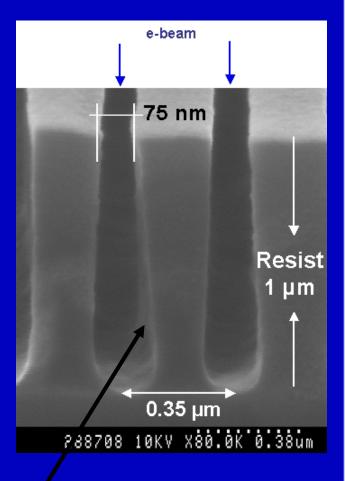


Electron beam exposure

Current dedicated systems have produced <u>line widths</u> of 10 nm or smaller

The primary advantage of electron beam lithography is that it is one way to <u>beat</u> the diffraction limit of light and make features in the nanometer regime

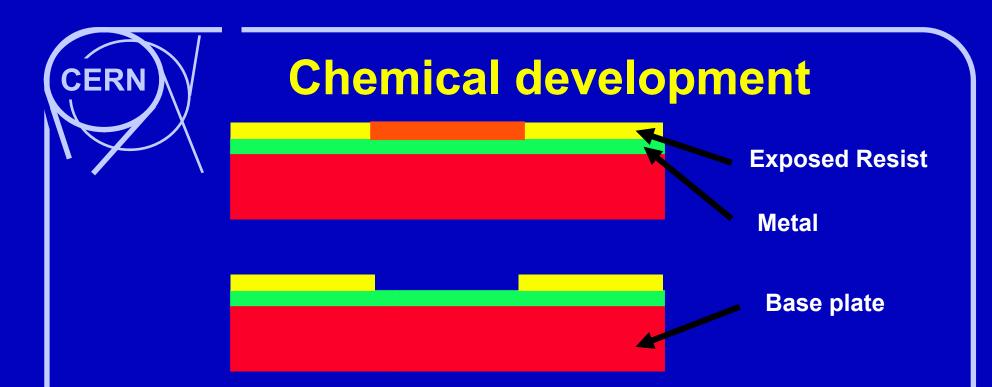
High accuracy but <u>sensitive</u> to <u>electric</u> and magnetic fields



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Electron scattering in resist Positive resist

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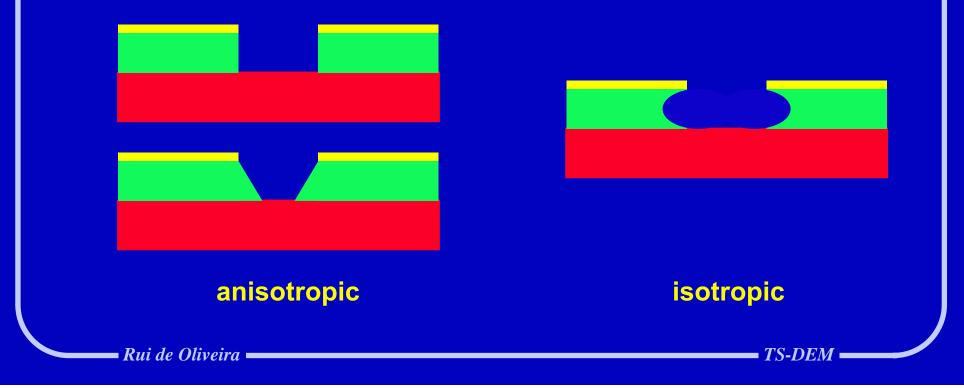
Horizontal spray chemical Development :acqueus or solvent

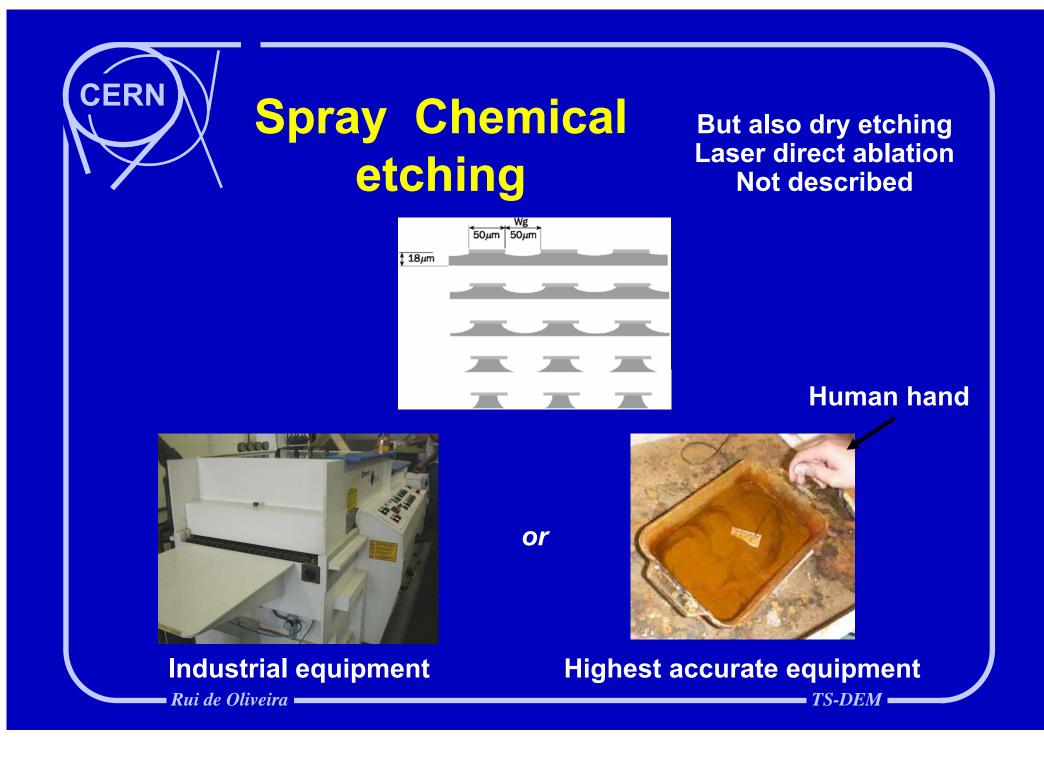




Etching

Most metals can be etched (isotropic etching)
Most Polymers also (isotropic etching)
Silicon etching can be anisotropic
Polyimide etching can be anisotropic







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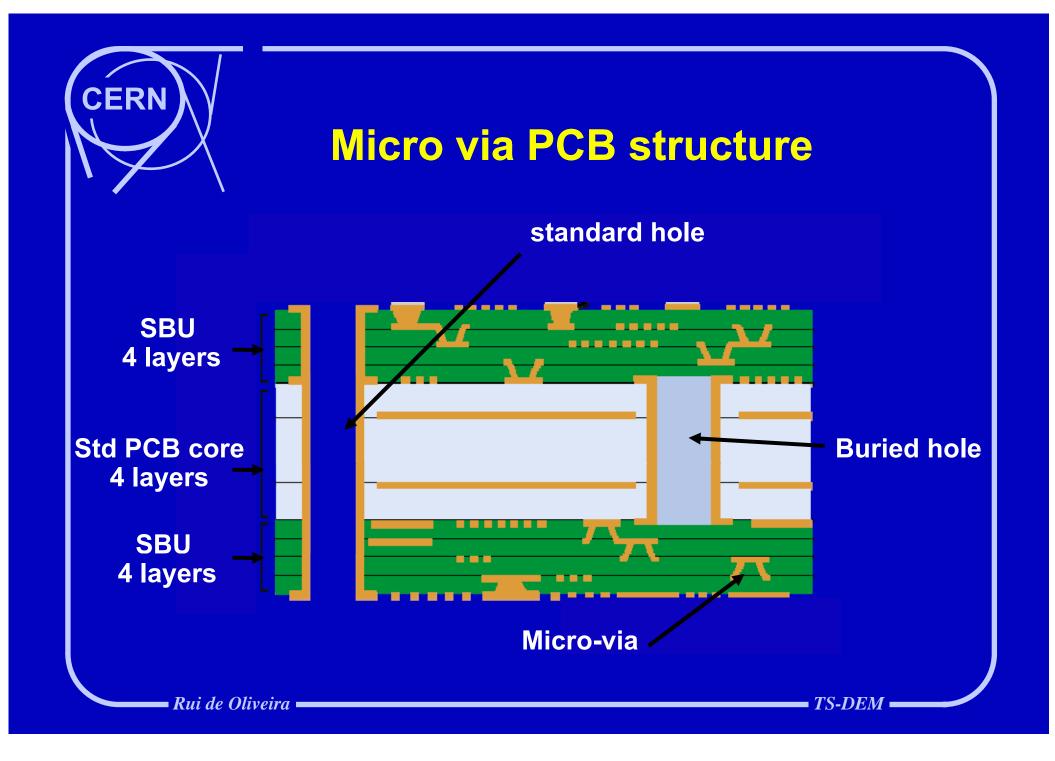
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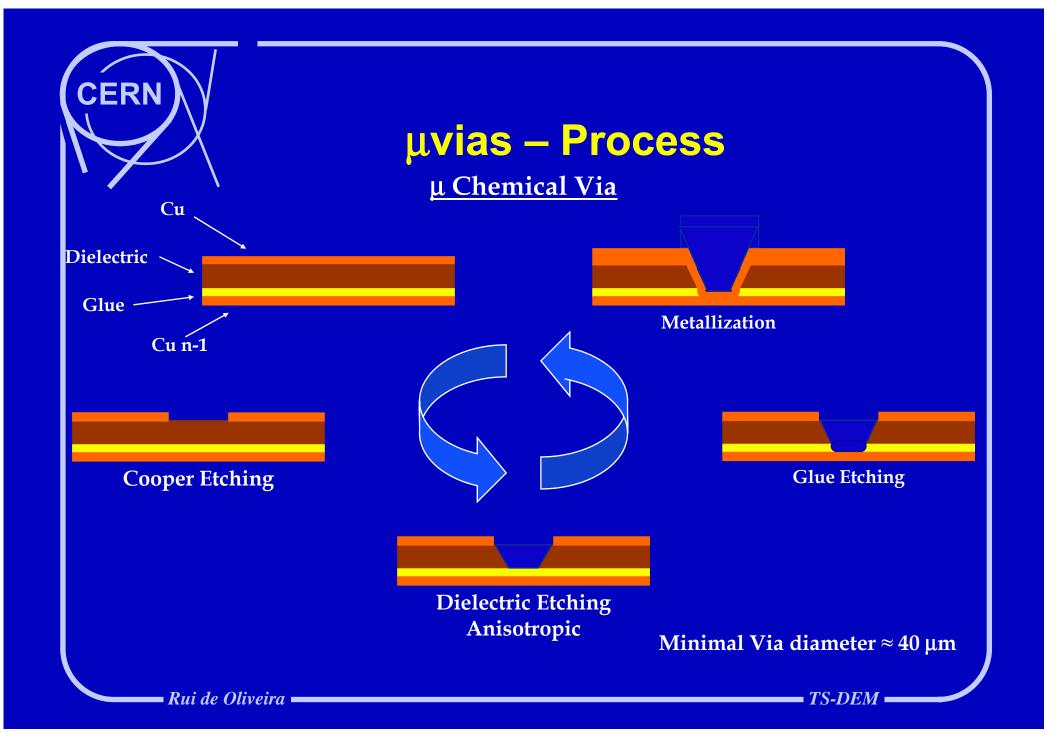
Photolithography at CERN

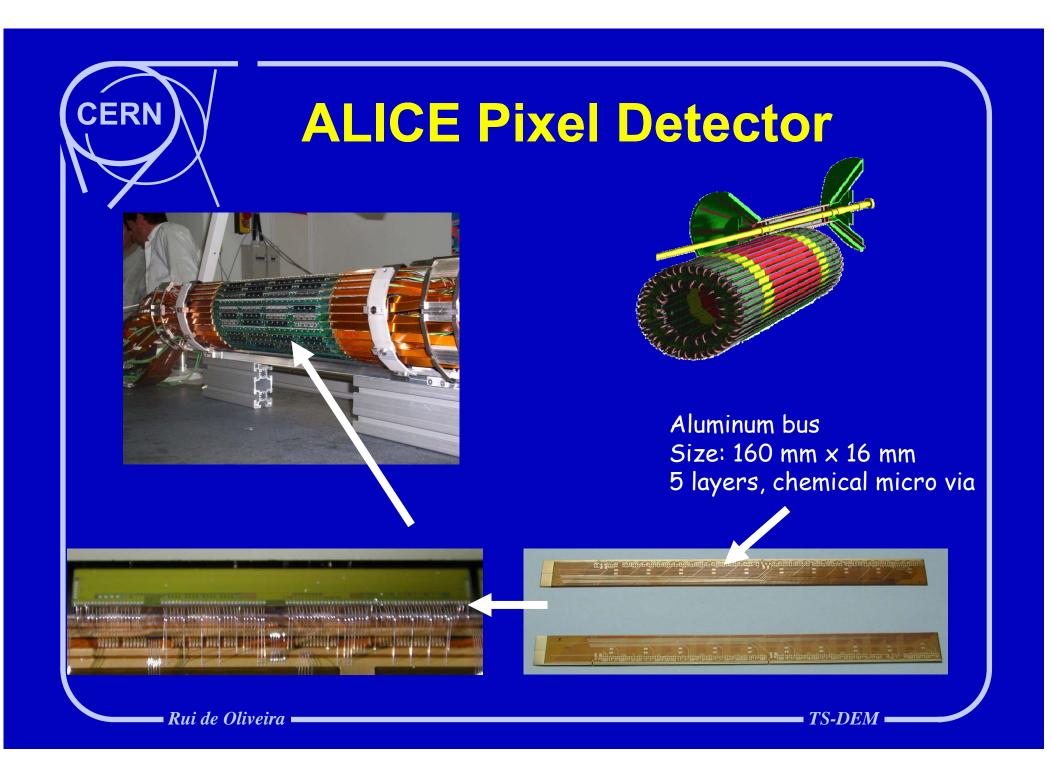
- fine line PCBs
- large size PCBs
- chemical micro-via circuits
- gas detectors

Conclusions

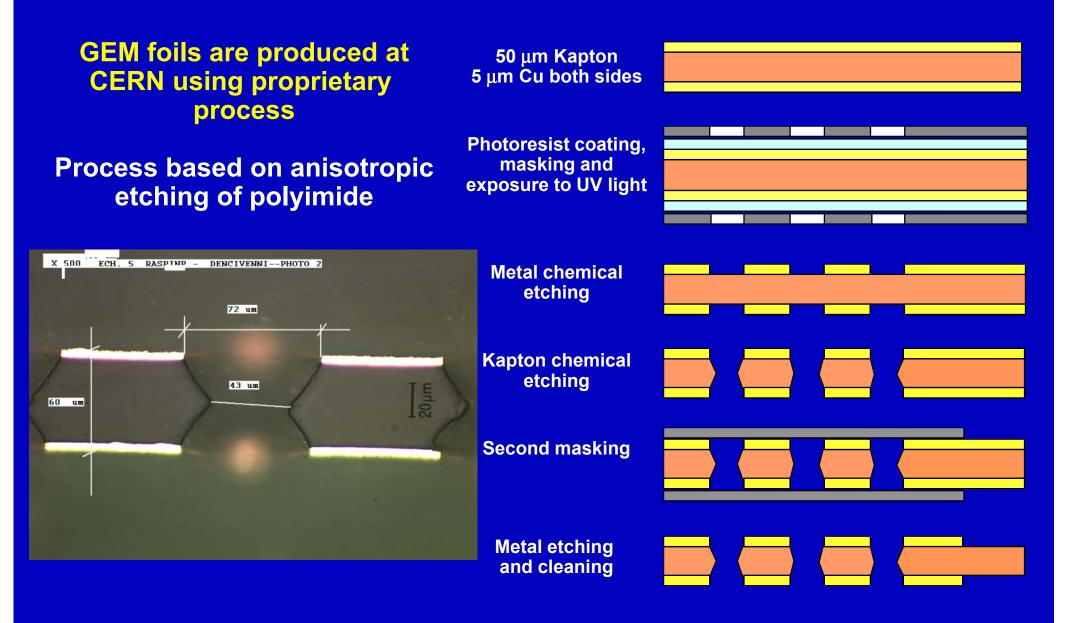






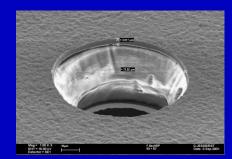


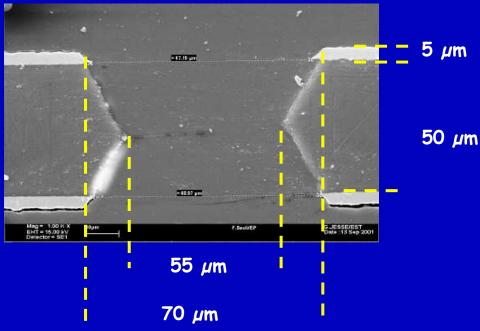
GEM manufacturing

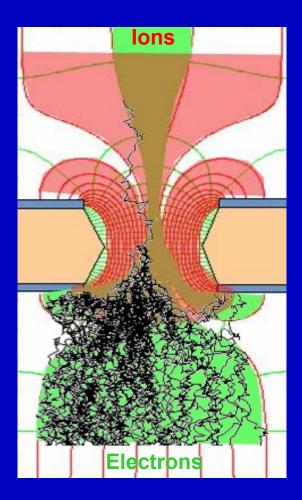


GEM operation principle Compared to each GEM foil.

A potential difference of ~500V is applied to each GEM foil. Primary electrons released by the radiation drift towards holes where the high electric field triggers an electron multiplication (avalanche) process





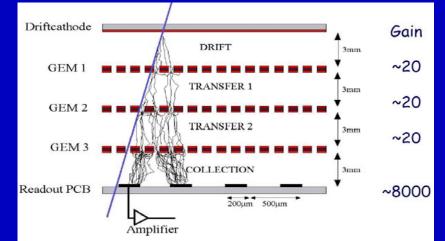


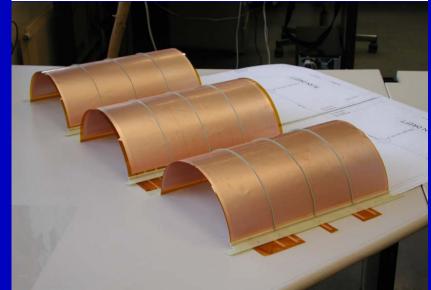
GEM detector

A GEM Detector consists of:

a drift electrode 3 GEM foils a readout electrode



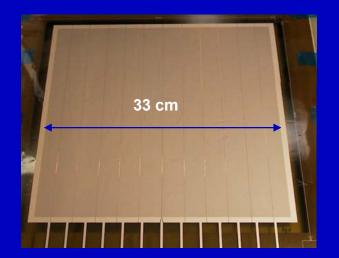


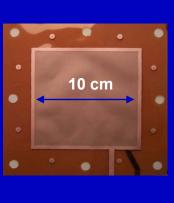


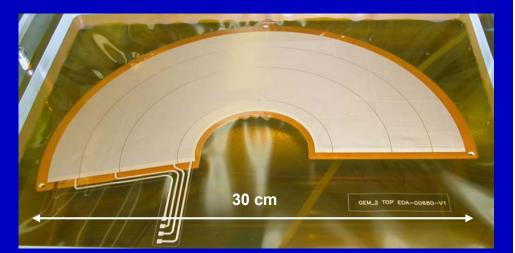
Semi-cylindrical GEM detector

GEM foils before being mounted into detector

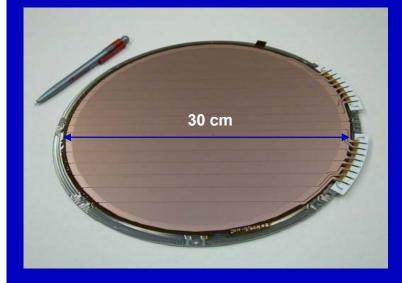
Examples of GEMs







25-200 µm holes, 50-300 µm pitch





Wide range of shapes and sizes

1500-2000 foils manufactured at CERN 1 cm² to 1000 cm²

Conclusions

Old technology but still the best to face future challenges

- PCB fabrication
- Semiconductor industry
- MEMs

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Easy to set up but extremely complicated for sub-micrometer range patterns

Future competition (cost still too high)

- Direct laser imaging, electron beam lithography
- Direct laser ablation

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